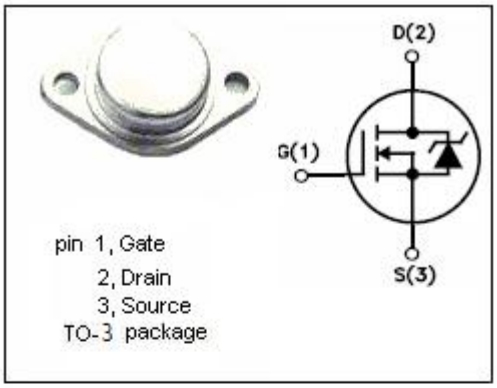
isc N-Channel MOSFET Transistor 2SK260

DESCRIPTION

- Drain Current –I_D=5A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 400V(Min)
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

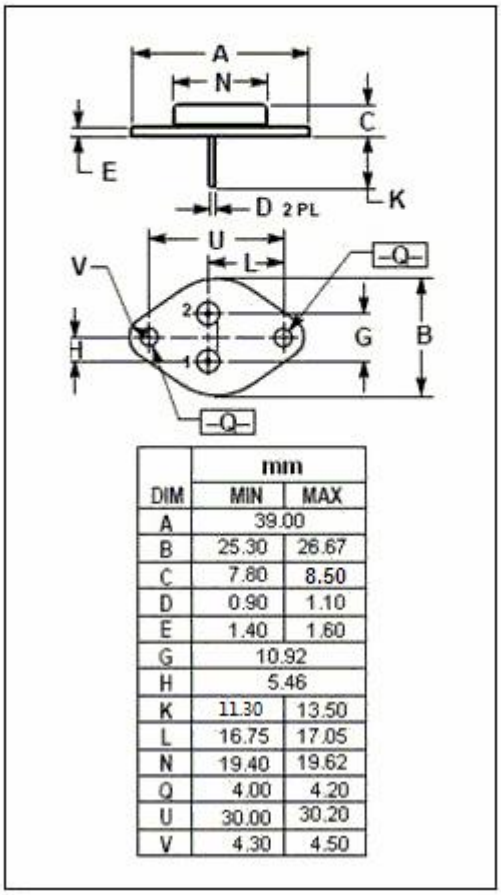
- Designed especially for high voltage,high speed applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	400	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=25℃	5	A
P_{tot}	Total Dissipation@TC=25℃	125	W
T_j	Max. Operating Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.67	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0; I_D= 10mA	400			V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D= 10mA	0.4		3.0	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= 15V; I_D= 3A		2.5	3.0	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±20V; V_{DS}= 0			±100	uA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=320V; V_{GS}= 0			1	mA
$V_{DS(ON)}$	Drain-Source Saturation Voltage	I_F= 3A; V_{GS}= 15V		7.5	9.5	V